**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	•						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	-	330	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	240	mA
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2.2	2.8	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	654	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$
4	S2	source TR2	☐1 ☐2 ☐3 <b>———</b> —————————————————————————————————	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
NX7002BKS	LT%

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor		_			
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	330	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	240	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	150	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	285	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	870	mW
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA
Per device						'
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 60 V, dual N-channel Trench MOSFET

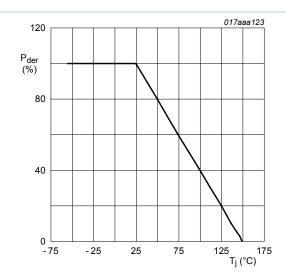


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

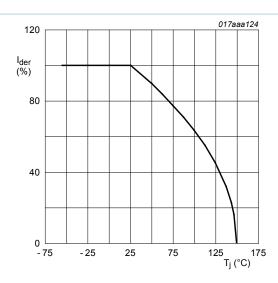
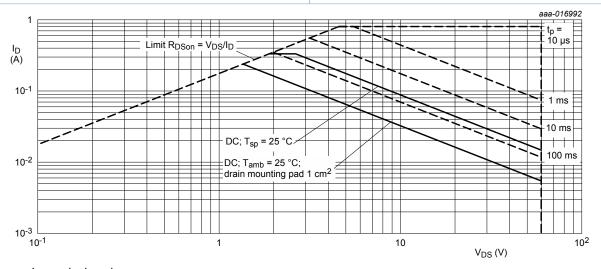


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



 $I_{DM}$  = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

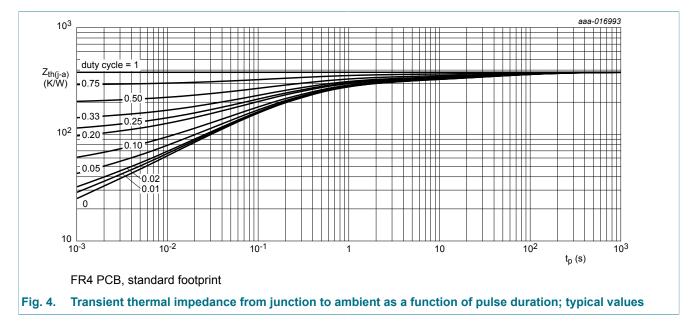
60 V, dual N-channel Trench MOSFET

## 9. Thermal characteristics

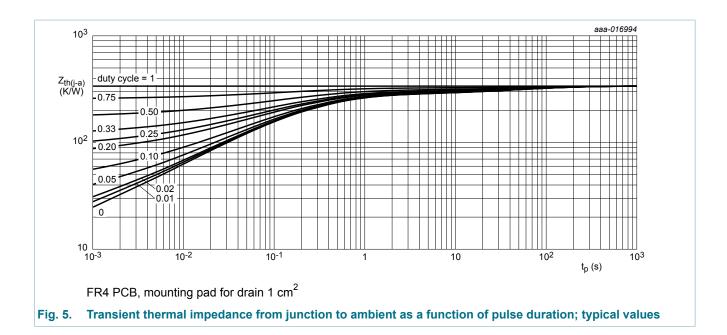
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
ung a)	thermal resistance		[1]	-	380	440	K/W
	from junction to ambient		[2]	-	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	125	145	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μA
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.2	2.8	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.5	5.7	Ω
		$V_{GS}$ = 5 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	2.5	3.2	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; $T_{j}$ = 25 °C	-	600	-	mS
$R_G$	gate resistance	f = 1 MHz	-	2.5	-	Ω
Dynamic c	haracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 30 V; $I_{D}$ = 200 mA; $V_{GS}$ = 10 V;	-	1	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	23.6	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	3	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	4.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	6.9	-	ns
t <sub>f</sub>	fall time		-	2.9	-	ns
Source-dra	in diode (per transistor)		ı	1	1	
V <sub>SD</sub>	source-drain voltage	$I_S = 50 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.87	1.2	V

#### 60 V, dual N-channel Trench MOSFET

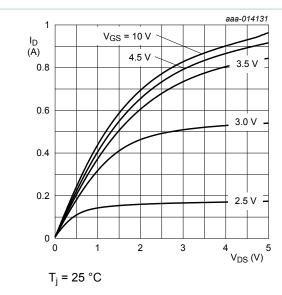


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

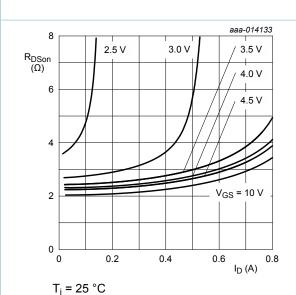
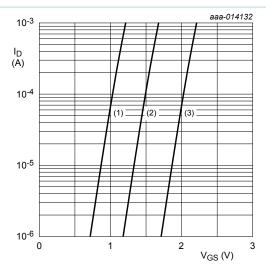


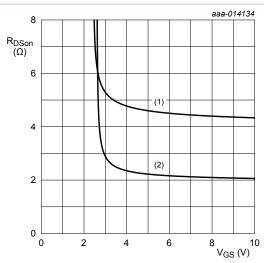
Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $T_j$  = 25 °C;  $V_{DS}$  = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



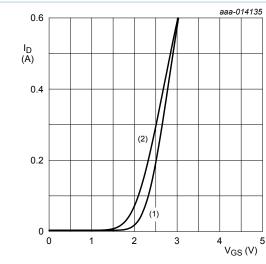
 $I_D = 0.2 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_{D} \times R_{DSon}$ 

(1)  $T_j = 25 \, ^{\circ}C$ 

(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

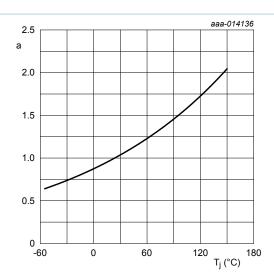
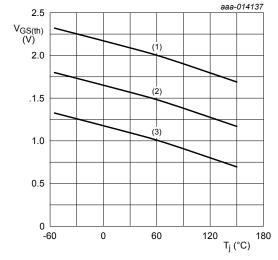


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

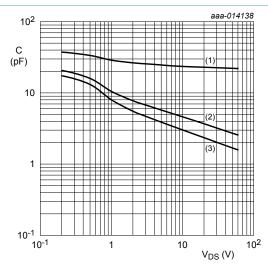
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3)  $C_{rss}$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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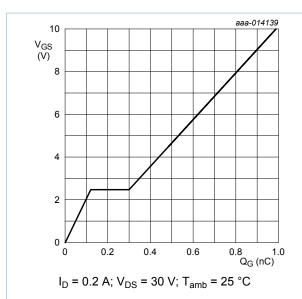


Fig. 14. Gate-source voltage as a function of gate charge; typical values

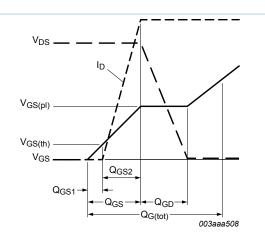
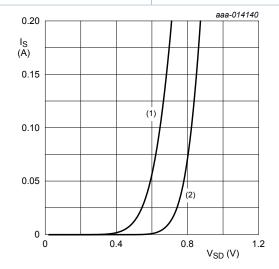


Fig. 15. MOSFET transistor: Gate charge waveform definitions



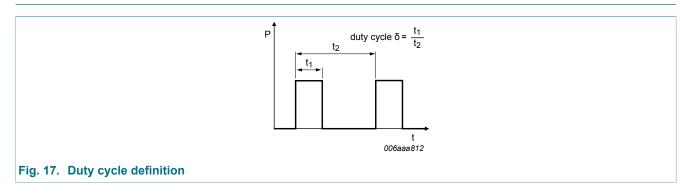
 $V_{GS} = 0 V$ (1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

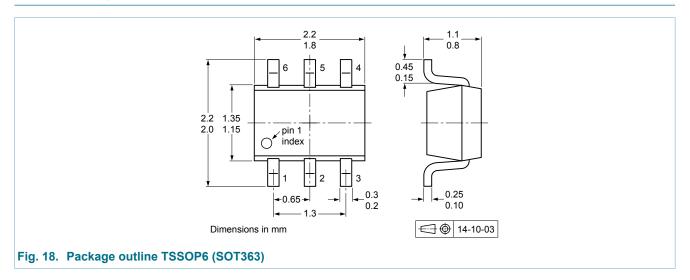
Fig. 16. Source current as a function of source-drain voltage; typical values

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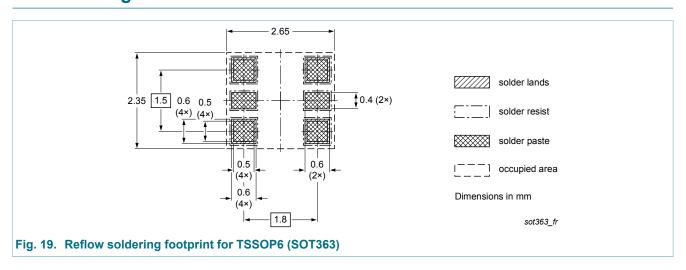
## 11. Test information



# 12. Package outline



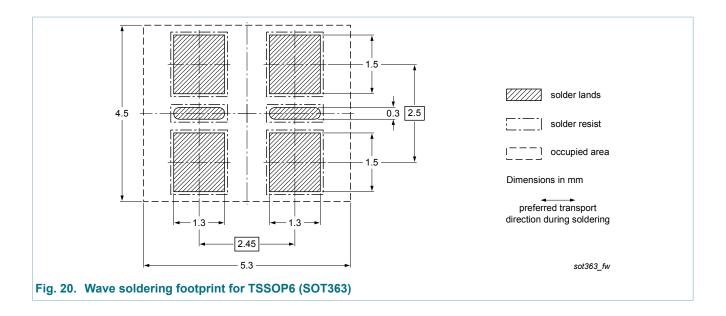
## 13. Soldering



NX7002BKS

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## **60 V, dual N-channel Trench MOSFET**



**60 V, dual N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKS v.1	20150512	Product data sheet	-	-

#### 60 V, dual N-channel Trench MOSFET

## 15. Legal information

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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